SEC.316
Patent No. 5,811,318

REISSUE PATENT APPLICATION DECLARATION

U.S. Patent 5,811,318, issued on September 22, 1998
(Attorney's Docket No.: SEC.316)

Applicant: Young-chan Kweon
Citizenship: Republic of Korea
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Title of Invention: METHOD FOR MANUFACTURING A LIQUID CRYSTAL DISPLAY

I, Young-chan Kweon, declare as follows:

1. The residence address and country of citizenship given above are true and correct.

2. I believe I am the original and first inventor of the invention claimed in the attached patent specification for which a reissue of United States Patent No. 5,811,318 (the '318 patent) is sought, and that I have reviewed and understand the contents of the attached specification, including its claims.

3. I believe that United States Patent No. 5,811,318 is wholly or partly inoperative by reason of my claiming less than I had a right to claim in the patent. These errors were discovered during a review of the patent claims after issuance. I believe the errors causing the insufficiencies arose without deceptive intention on the part of the applicant. I believe the attorney prosecuting the application failed to appreciate the full scope of the invention.

4. One insufficiency or error concerns the scope of method claims 1-15, and more particularly, to claims 1 and 8, which each claim seven steps: the first is forming a gate electrode and a gate pad; the second is forming an insulated film; the third is forming a semiconductor film pattern; the fourth is forming a source/drain electrode and a pad electrode, or forming a source electrode and /or a drain electrode; the fifth is forming a passivation layer; the sixth is exposing a first metal film; and the seventh is forming a pixel electrode. The relevant clauses of claims 1 and 8 have been highlighted below:

> 1. A method for manufacturing a liquid crystal display, comprising the steps of:
> forming a gate electrode and a gate pad by depositing a first metal film and a second metal film over a substrate in a TFT area and a gate-pad connecting area, respectively, by a first photolithography process;
> forming an insulated film over the gate electrode and the gate pad;
> forming a semiconductor film pattern over the insulating film in the TFT area by a second photolithography process;
> forming a source electrode/drain electrode and pad electrode in the TFT portion and the pad portion, respectively, using a third photolithography process, the source electrode/drain electrode and the pad electrode all being comprised of a third metal film;
> ***forming a passivation film pattern by a fourth photolithography process, the passivation film exposing a portion of the drain electrode, a portion of the gate pad, and a portion of the pad electrode;***
> exposing the first metal film by etching a portion of the second metal film that comprises the gate pad using the passivation film pattern as a mask; and
> ***forming a pixel electrode connected to the drain electrode of the TFT area by a fifth photolithography process, the pixel electrode acting to connect the gate pad of the gate-pad connecting area to the pad electrode of the pad area.***

8. A method for manufacturing a liquid crystal display, comprising the steps of:

forming a gate electrode and a gate pad by depositing a first metal film and a second metal film over a substrate in a TFT area and a pad area, respectively, by a first photolithography process;

forming an insulated film over the gate electrode and the gate pad;

forming a semiconductor film pattern over the insulating film in the TFT area by a second photolithography process;

forming a source electrode and a drain electrode in the TFT area by a third photolithography process, the source electrode and the drain electrode comprising a third metal film;

forming a passivation film pattern that exposes a portion of the drain electrode on the TFT area and a portion of the gate pad of the pad area by forming a passivation film over the source electrode and the drain electrode and performing a fourth photolithography process on the passivation film and the insulating film;

exposing the first metal film of the pad area by etching the second metal film using the passivation film pattern as a mask; and

forming a pixel electrode that is connected to the drain electrode of the TFT area and contacts the first metal film of the pad area by a fifth photolithography process.

5. I still maintain the prior art is distinguished by claim 1 above. However, I also believe the prior art would be distinguished by claiming the step of forming a passivation film as including the sub-step of etching the insulated layer over the portion of the gate pad.

6. I also believe that it would be appropriate to further define the forming of a pixel electrode to include forming a first pixel electrode pattern connected to the drain electrode of the TFT area and a second pixel electrode pattern acting to connect to the gate past of the gate-pad connecting area to the pad electrode of the pad area using a fifth photolithography process, and that if claim 1 contained such a recitation, it would continue to distinguish over the prior art.

7. I therefore believe that claim 1, as broadened below would be properly distinguished over the prior art.

> 1. A method for manufacturing a liquid crystal display, comprising the steps of:
> forming a gate electrode and a gate pad by depositing a first metal film and a second metal film over a substrate in a TFT area and a gate-pad connecting area, respectively, by a first photolithography process;
> forming an insulated film over the gate electrode and the gate pad;
> forming a semiconductor film pattern over the insulating film in the TFT area by a second photolithography process;
> forming a source electrode/drain electrode and pad electrode in the TFT portion and the pad portion, respectively, using a third photolithography process, the source electrode/drain electrode and the pad electrode all being comprised of a third metal film;
> forming a passivation film pattern [by a fourth photolithography process, the passivation film] exposing a portion of the drain electrode, a portion of the gate pad, and a portion of the pad electrode, and etching the insulating layer over the portion of the gate pad, by a fourth photolithography process;
> exposing the first metal film by etching a portion of the second metal film that comprises the gate pad using the passivation film pattern as a mask; and

forming a first pixel electrode pattern connected to the drain electrode of the TFT area [by a fifth photolithography process, the pixel electrode acting to connect the gate pad of the gate-pad connecting area to the pad electrode of the pad area] and a second pixel electrode pattern acting to connect to the gate past of the gate-pad connecting area to the pad electrode of the pad area using a fifth photolithography process.

8. I still maintain the prior art is distinguished by claim 8 above. However, I also believe the prior art would be distinguished by claiming the step of forming a pixel electrode pattern to include forming a first pixel electrode pattern connected to the drain electrode of the TFT area and a second pixel electrode pattern which is connected to the first film of the pad area by a fifth photolithography process.

9. I therefore believe that claim 8, as broadened below would be properly distinguished over the prior art.

8. A method for manufacturing a liquid crystal display, comprising the steps of:
forming a gate electrode and a gate pad by depositing a first metal film and a second metal film over a substrate in a TFT area and a pad area, respectively, by a first photolithography process;
forming an insulated film over the gate electrode and the gate pad;
forming a semiconductor film pattern over the insulating film in the TFT area by a second photolithography process;
forming a source electrode and a drain electrode in the TFT area by a third photolithography process, the source electrode and the drain electrode comprising a third metal film;
forming a passivation film pattern that exposes a portion of the drain electrode on the TFT area and a portion of the gate pad of the pad area by forming a passivation film

over the source electrode and the drain electrode and performing a fourth photolithography process on the passivation film and the insulating film;

exposing the first metal film of the pad area by etching the second metal film using the passivation film pattern as a mask; and

forming a first pixel electrode pattern that is connected to the drain electrode of the TFT area [and contacts] and a second pixel electrode pattern that is connected to the first metal film of the pad area by a fifth photolithography process.

10. These beliefs are based on a review of the prosecution history of Application No. 770,796 which issued as the '318 patent. The '318 patent discloses the steps of forming a passivation film pattern by a fourth photolithography process, and forming a pixel electrode. (see, e.g., Figs. 10 and 12; col. 5, line 52, through col. 6, line 13, and Fig. 16; col. 6., line 62, through col. 7, line 16). The Patent Office determined that the prior art did not teach the variously-recited steps of forming a pixel electrode, regardless of how the step of forming a passivation film pattern was recited. (See, e.g., the Notice of Allowability of February 26, 1998, at 5).

11. The Patent Office specifically determined that the cited prior art combination did not teach forming a pixel electrode acting to connect the gate pad of the gate-pad connecting area to the pad electrode of the pad area, nor did it disclose forming a pixel electrode that is connected to the drain electrode of the TFT area and contacts the first metal film of the pad area by a fifth photolithography process. (See, e.g., the Notice of Allowability of February 26, 1998, at 5).

12. I also believe the attorney erred by not drafting another set of claims based on the patentable apparatus including a pixel electrode that contacts the drain electrode and

the first metal film. Accordingly, I believe the claims were overly narrowed causing an error during the initial prosecution of this application as a result of the attorney only filing method claims in the present invention.

13. We therefore propose to broaden the claims by adding the following new claims, which focus on a TFT substrate.

The proposed independent claim would be as follows.

16. A TFT substrate, comprising:
a gate electrode comprising a first metal film over a substrate and a second metal film over the first metal film;
a gate pad comprising the first metal film and a portion of a removed area of the second metal film;
an insulated film over the gate electrode and having an exposed area of the first metal film of the gate pad;
a semiconductor film pattern over the insulating film;
a source electrode formed over a first portion of the semiconductor film pattern;
a drain electrode formed over a second portion of the semiconductor film pattern;
a passivation film pattern formed over the source electrode, having a contact hole over the drain electrode and having an exposed area of the first metal film of the gate pad;
a first pixel electrode pattern electrically contacted to the drain electrode on the passivation film pattern; and
a second pixel electrode pattern electrically contacted to the exposed area of the first metal film of the gate pad.

The proposed dependent claims would be as follows:

17. A TFT substrate, as recited in claim 16, wherein the first metal film comprises a refractory metal.

18. A TFT substrate, as recited in claim 17, wherein the first metal film comprises a material selected from the group consisting of Cr, Ta, Mo, and Ti.

19. A TFT substrate, as recited in claim 16, wherein the second metal film comprises Al or an Al alloy.

20. A TFT substrate, as recited in claim 16, wherein the insulating material comprises a nitride film SiN_x.

21. A TFT substrate, as recited in claim 16, wherein the first and second pixel patterns comprise ITO.

22. A TFT substrate, as recited in claim 16, wherein a portion of the passivation film directly contacts the semiconductor film pattern.

14. The present specification of U.S. Patent 5,811,318 (the '318 patent) provides ample support for the new claims. The specification of the '318 patent discloses a gate electrode formed from stacked first and second metal films 31 and 33 (See, Fig. 7; col. 4, line 63, through col. 5, line 12); a gate pad also made from portions of the first and second metal films 31 and 33 (See, Fig. 7; col. 5, lines 6-12); an insulated film 35 formed over the gate electrode and exposing area of the first metal film 33 of the gate pad (See, Figs. 8-11; col. 5, lines 23-27, col. 5, lines 59-62); a semiconductor film pattern 37 and 39 formed over the insulating film 35 (See, Fig. 8; col. 5, lines 23-38); a source electrode 41a formed over a first portion of the semiconductor film pattern 37 and 39 (See, Fig. 9; col. 5, lines 39-50); a drain electrode 41b formed over a second portion of the semiconductor film pattern 37 and 39 (See, Fig. 9; col. 5, lines 39-50); a passivation film pattern 43 formed over the source electrode 41a and the drain electrode 41b, having a contact hole over the drain electrode 41b and having contact hole over the exposed area of the first metal film 33 of the gate pad (See, Fig. 11; col. 5, line 65, through col. 6, line 4); a first pixel electrode pattern 47 electrically contacted to the drain electrode 41b (See, Fig. 12; col. 6, lines 5-13); and a second pixel electrode pattern 47 electrically contacted to the exposed area of the first metal film 33 of the gate pad (See, Fig. 12; col. 6, lines 5-13).

15. The specification of the '318 patent also discloses that the first metal film 31 may be made of a refractory metal, such as Cr, Ta, Mo, or Ti and that the second metal film 33 may be a material such as Al, or an Al alloy. (See, col. 4, line 64, through col. 5,

line 5). Furthermore, it discloses that the insulating film 35 may be made of a nitride film SiN_x (See, col. 5, lines 24-26, and col. 6, lines 41-49), and that the first and second pixel patterns 47 may be made of ITO. (See, col. 6, lines 5-11).

16. The specification of the '318 patent also discloses that a portion of the passivation film 43 directly contacts the semiconductor film pattern 37 and 39. (See, Fig. 10).

17. The Patent Office determined that the prior art did not teach the formation of a pixel electrode that is connected to the to the drain electrode of the TFT area and contacts the first metal film of the pad area. (See, e.g., the Notice of Allowability of February 26, 1998, at 5). Just as the formation of these elements is not shown, so too are the elements themselves not shown.

18. In view of the above, I believe the prior art is clearly distinguished by at least the formation of the first and second pixel electrodes, and the first and second pixel electrodes themselves, as indicated by the Patent Office. The prosecuting attorney did not appreciate the full scope and true nature of the invention in light of the prior art. I believe the prosecuting attorney inadvertently erred by insufficiently reciting the step in claim 1 of forming a passivation layer as not including a etching sub-step, and by narrowing claims 1 and 8 by limiting the first pixel electrode to a single pixel electrode pattern. I also believe that the prosecuting attorney inadvertently erred by not providing a set of apparatus claims for this application.

19. I acknowledge my duty to disclose information of which I am aware is material to the examination of this application. I understand that information is material where there is a substantial likelihood that a reasonable patent examiner would consider it important in deciding whether to allow the attached application to issue as a patent. Accordingly, a separate Information Disclosure Statement is forwarded herewith.

I further declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United State Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

Dated: 24 August 2000.

Young chan Kweon

RULE 63 (37 C.F.R. 1.63)
COMBINED DECLARATION AND POWER OF ATTORNEY
FOR PATENT APPLICATION
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

FOR UTILITY/DESIGN
CIP/PLANT
ORIGINAL/SUBSTITUTE
DECLARATIONS

As a below named inventor, I hereby declare that my residence, post office address and citizenship are as stated below next to my name, and I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled: **Method for Manufacturing a Liquid Crystal Display**

the specification of which (CHECK applicable BOX(ES))
[ ] is attached hereto
[XX] was filed on **December 20, 1996** of U.S. Application No. **08/770,796.**
[ ] was filed as PCT International Application No. PCT/_____
on _____.
and (if applicable to U.S. or PCT application) was amended on _____.

I hereby state that I have reviewed and understand the contents of the above-identified specification, including claims (as amended by any amendment referred to above). I acknowledge the duty to disclose information which is material to the examination of this application in accordance with 37 C.F.R. 1.56(a). I hereby claim foreign priority benefits under 35 U.S.C. 119/365 of any foreign application(s) for patent or inventor's certificate listed below and have also identified below any foreign application(s) for patent or inventor's certificate filed by me or my assignee disclosing the subject matter claimed in this application and having a filing date (1) before that of the application on which priority is claimed, or (2) if no priority is claimed, before the filing date of this application:

PRIOR FOREIGN APPLICATION(S)			Priority Claimed	
Number	Country	Day/MONTH/Year Filed	YES	NO
95-62170	**Korea**	**28/DECEMBER/1995**	**X**	
96-18516	**Korea**	**29/MAY/1996**	**X**	

I hereby claim the benefit under 35 U.S.C. 120/365 of all United States applications listed below and PCT International applications listed above or below and, insofar as the subject matter of each of the claims of this application is not disclosed in such prior applications in the manner provided by the first paragraph of 35 U.S.C. 112, I acknowledge the duty to disclose material information as defined in 37 C.F.R. 1.56(a) which occurred between the filing date of each such prior application and the national or PCT international filing date of this application:

PRIOR U.S. OR PCT APPLICATION(S)

Application No. (series code/serial number)	Day/MONTH/Year Filed	Status pending, abandoned, patented

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

And I hereby appoint Samsung Electronics Co, Ltd., 1200 New Hampshire Avenue, N.W. Suite 550, Washington, D.C. 20036, telephone number (202) 296-0227 (to whom all communications are to be directed), and the below named attorneys to prosecute this application and to transact all business in the Patent and Trademark Office connected therewith and with the resulting patent, and I hereby authorize them to act and rely on instructions from and communicate directly with the person/assignee/attorney/firm/organization who/which first sends/sent this case to them and by whom/which I hereby declare that I have consented after full disclosure to be represented unless/until I instruct Samsung Electronics in writing to the contrary.

Charles R. Donohoe	24,546	Brian C. Altmiller	37,271
Neil A. Steinberg	34,735	Allen LeRoy Limberg	27,211
William L. Geary, Jr.	35,879		

1) Inventor's signature Young-chan Kweon Date FEB.14, 1997

Inventor's Name:	**Young-chan**		**Kweon**	**Korean**
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2) Inventor's signature _____ Date _____

Inventor's Name:				
	First	M.I.	Family Name	Citizenship
Residence (City)			State/Foreign Country	Rep. of Korea
Post Office Address including Zip Code				

3) Inventor's signature _____ Date _____

Inventor's Name:				
	First	M.I.	Family Name	Citizenship
Residence (City)			State/Foreign Country	Rep. of Korea
Post Office Address including Zip Code				

4) Inventor's signature _____ Date _____

Inventor's Name:				
	First	M.I.	Family Name	Citizenship
Residence (City)			State/Foreign Country	Rep. of Korea
Post Office Address including Zip Code				

FOR ADDITIONAL INVENTORS, check box [ ] and attach sheet (SEC-100/2) for same information for each re: signature, name, date, citizenship, residence and address.

SEC.316RE
Patent No. 5,811,318

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Reissue Application of)
)
Patent No.: 5,811,318)
)
Serial No.: 09/667,643)
)
Issued: September 22, 2000)
)
To: Young-chan Kweon)
)
Title: METHOD FOR MANUFACTURING)
A LIQUID CRYSTAL DISPLAY)
)

Commissioner of Patents and Trademarks
Washington, D.C. 20231

APPOINTMENT OF ASSOCIATE ATTORNEY

Sir:

The undersigned, the assignee of and to the entire right, title and interest of the above referenced Letters Patent, hereby appoints Adam C. Volentine (Registration No. 33,289), William Francos (Registration No. 38,456), and their associate attorneys to prosecute said reissue application and to transact all business in the Patent and Trademark Office therewith.

Correspondence should be directed to Kenneth D. Springer at the following address:

Volentine Francos, PLLC
12200 Sunrise Valley Drive, Suite 150
Reston, Virginia 20191
(703) 715-0870

Please direct all telephone calls to Mr. Springer at (703) 264-3526.

SEC.316RE
Patent No. 5,811,318

I, the undersigned, am empowered to sign this Appointment of Associate Attorney on behalf of the assignee.

SAMSUNG ELECTRONICS CO., LTD.

By: Jongsoo Yoon
Jong-soo Yoon
Title: Senior Engineer

PTO/SB/53 (02-01)
Approved for use through 01/31/2004. OMB 0651-0033
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

REISSUE APPLICATION: CONSENT OF ASSIGNEE; STATEMENT OF NON-ASSIGNMENT	Docket Number (Optional) SEC.316RE

This is part of the application for a reissue patent based on the original patent identified below.

Name of Patentee(s) Young-chan Kweon	
Patent Number 5,811,318	Date Patent Issued
Title of METHOD FOR MANUFACTURING A LIQUID CRYSTAL DISPLAY	

1. ☒ Filed herein is a statement under 37 CFR 3.73(b). (Form PTO/SB/96)

2. ☐ Ownership of the patent is in the inventor(s), and no assignment of the patent is in effect.

One of boxes 1 or 2 above must be checked. If multiple assignees, complete this form for each assignee. If box 2 is checked, skip the next entry and go directly to "Name of Assignee".

The written consent of all assignees and inventors owning an undivided interest in the original patent is included in this application for reissue.

The assignee(s) owning an undivided interest in said original patent is/are Samsung Electronics Co., Ltd. and the assignee(s) consents to the accompanying application for reissue.

The undersigned (whose title is supplied below) is empowered to sign this Consent of Assignee on behalf of assignee.

Name of assignee/inventor (if not assigned)	
Signature Jongsoo Yoon	Date Dec 18 2002

Typed or printed name and title of person signing for assignee (if assigned)

Jong-soo Yoon, Senior Engineer

PTO/SB/96 (2-98)
Approved for use through 09/30/2000. OMB 0651-0031
Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE
Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.

STATEMENT UNDER 37 CFR 3.73(b)

Applicant: Young-chan Kweon

Application No.: 09/667,643 Filed: September 22, 2000

Entitled: Method for manufacturing a Liquid Crystal Display

Samsung Electronics Co., Ltd., a corporation
(Name of Assignee) (Type of Assignee, e.g., corporation, partnership, university, government agency, etc.)

states that it is:

1. [☑] the assignee of the entire right, title, and interest; or

2. [ ] an assignee of an undivided part interest

in the patent application identified above by virtue of either:

A. [☑] An assignment from the inventor(s) of the patent application identified above. The assignment was recorded in the Patent and Trademark Office at Reel 8410, Frame 0751, or for which a copy thereof is attached.

OR

B. [ ] A chain of title from the inventor(s), of the patent application identified above, to the current assignee as shown below:

1. From: _____ To: _____
The document was recorded in the Patent and Trademark Office at
Reel _____, Frame _____, or for which a copy thereof is attached.

2. From: _____ To: _____
The document was recorded in the Patent and Trademark Office at
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3. From: _____ To: _____
The document was recorded in the Patent and Trademark Office at
Reel _____, Frame _____, or for which a copy thereof is attached.

[ ] Additional documents in the chain of title are listed on a supplemental sheet.

[☑] Copies of assignments or other documents in the chain of title are attached.

The undersigned (whose title is supplied below) is empowered to sign this statement on behalf of the assignee.

Dec 18 2002
Date

Jongsoo Yoon
Signature

Jong-soo Yoon
Typed or printed name

Senior Engineer
Title

UNITED STATES DEPARTMENT OF COMMERCE
Patent and Trademark Office
ASSISTANT SECRETARY AND COMMISSIONER
OF PATENTS AND TRADEMARKS
Washington, D.C. 20231

MAY 13, 1997

PTAS

100381705A

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UNITED STATES PATENT AND TRADEMARK OFFICE
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RECORDATION DATE: 03/10/1997

REEL/FRAME: 8410/0751
NUMBER OF PAGES: 3

BRIEF: ASSIGNMENT OF ASSIGNOR'S INTEREST (SEE DOCUMENT FOR DETAILS).

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KWEON, YOUNG-CHAN

DOC DATE: 02/14/1997

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SERIAL NUMBER: 08770796
PATENT NUMBER:

FILING DATE: 12/20/1996
ISSUE DATE:

MAYA BENNETT, EXAMINER
ASSIGNMENT DIVISION
OFFICE OF PUBLIC RECORDS

REISSUE PATENT APPLICATION STATEMENT AS TO LOSS OF ORIGINAL PATENT	Docket Number (Optional) SEC.316RE

I hereby state that:

I am the applicant for a reissue patent based on the original patent identified below.

Name of inventor(s)/Assignee(s) **Young-chan KWEON**

Patent Number **5,811,918**

Title of invention **METHOD FOR MANUFACTURING A LIQUID CRYSTAL DISPLAY**

Reissue application number (if known) **09/667,643**

The ribboned original patent grant is lost or inaccessible

Signature ✓ Young Chan Kweon

Typed or printed name	Date ✓
Young-chan KWEON	2002/09/10

Title (e.g., inventor(s), officer of assignee)

Inventor